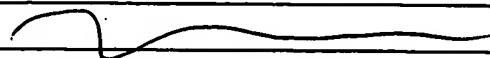


FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  <b>INFORMATION DISCLOSURE STATEMENT          BY APPLICANT</b>  (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. ASMJP.085DV1	APPLICATION NO. Filed herewith 10/783,044
	APPLICANT Michael A. Todd	
	FILING DATE Filed Herewith	GROUP Unknown 1775

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
A	1.	4,781,942	11/01/88	Leyden et al.	T	T	
	2.	4,863,755	09/05/89	Hess et al.			
	3.	4,894,352	01/16/90	Lane et al.			
	4.	4,992,306	02/12/91	Hochberg et al.			
	5.	5,011,706	04/30/91	Tarhay et al.			
	6.	5,028,566	07/02/91	Legendijk			
	7.	5,231,058	07/27/93	Maeda et al.			
	8.	5,240,813	08/31/93	Watanabe et al.			
	9.	5,244,698	09/14/93	Ishihara et al.			
	10.	5,314,724	05/24/94	Tsukune et al.			
	11.	5,324,539	06/28/94	Maeda et al.			
	12.	5,380,555	01/10/95	Mine et al.			
	13.	5,433,786	07/18/95	Hu et al.			
	14.	5,494,712	02/27/96	Hu et al.			
	15.	5,554,570	09/10/96	Maeda et al.			
	16.	5,563,105	10/08/96	Dobuzinsky et al.			
	17.	5,703,404	12/30/97	Matsuura			
	18.	5,840,821	11/24/98	Nakano et al.			
	19.	5,876,798	03/02/99	Vassiliev			
	20.	5,989,998	11/23/99	Sugahara et al.			
	21.	5,998,522	12/07/99	Nakano et al.			
	22.	6,004,730	12/21/99	Mikoshiba et al.			
	23.	6,045,877	04/04/00	Gleason et al.			
	24.	6,051,321	04/18/00	Lee et al.			
	25.	6,051,508	04/18/00	Takase et al.			
	26.	6,054,379	04/25/00	Yau et al.			
	27.	6,068,884	05/30/00	Rose et al.			

EXAMINER 	DATE CONSIDERED 11/05
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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMJP.065DV1	APPLICATION NO. Filed herewith <b>10/763,048</b>
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Michael A. Todd	
		FILING DATE Filed Herewith	GROUP Unknown <b>1775</b>

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS FILING DATE (IF APPROPRIATE)
<b>JA</b>	28.	6,245,690	08/12/01	Yau et al.	<b>I</b>	<b>I</b>
<b>JA</b>	29.	6,258,407	07/10/01	Lee et al.	<b>I</b>	<b>I</b>
	30.	6,303,047	10/16/01	Aronowitz et al.	<b>I</b>	<b>I</b>
	31.	6,340,628	01/22/02	Van Cleemput et al.	<b>I</b>	<b>I</b>
<b>JA</b>	32.	6,458,718	10/01/02	Todd	<b>I</b>	<b>I</b>

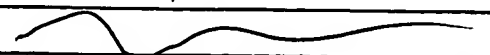
FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
JA	33.	EP 0 436 185 B1	03/20/96	EPO	I	I		
	34.	EP 0 706 216 A2	04/10/96	Europe				
	35.	EP 0 723 600 B1	07/07/99	EPO				
	36.	EP 0 771 886 A1	05/07/97	EPO				
	37.	EP 0 960 958 A2	12/01/99	EPO				
	38.	EP 0 935 283 A2	08/11/99	EPO				
	39.	EPO 367 004 B1	12/15/93	EPO				
	40.	JP 09 293716A	11/11/97	Japan				
	41.	JP 11 176329 A	07/02/99	Japan				
	42.	WO 97/40207	10/30/97	PCT				
	43.	WO 97/41592	11/06/97	PCT				
	44.	WO 99/21706	05/06/99	PCT				
	45.	WO 99/41423	08/19/99	PCT				
	46.	WO 99/55526	11/04/99	PCT				
	47.	WO 99/60621	11/25/99	PCT				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
<b>JA</b>	48. Bayer et al., Overall kinetics of SiO <sub>x</sub> remote-PECVD using different organosilicon monomers, Surface and Coatings Technology, 116-119 (1999) 874-878

EXAMINER	DATE CONSIDERED <b>11/05</b>
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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMJP.06SDV1	APPLICATION NO. Filed herewith <b>107783,044</b>
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Michael A. Todd	
		FILING DATE Filed Herewith	GROUP Unknown <b>1778</b>

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
<b>A</b>	49. Berjoan et al., <i>XPS and XPS valence band characterizations of amorphous or polymeric silicon based thin films prepared by PACVD from organosilicon monomers</i> , J. Phys. IV France 9 (1999) pp. 1059-1068.
	50. C.A. Costello and J.J. McCarthy, "Introduction of Organic Functional Groups onto the Surface of Poly(tetrafluoroethylene)," Proceedings of the ACS Division of Polymeric Materials Science and Engineering, Vol. 55 p. 893 (1986).
	51. Chandrasekhar et al., "New Silicon-Carbon Materials Incorporating Si4C Building Blocks," Mat. Res. Soc. Symp. Proc., Vol. 441, Materials Research Society, (1997)
	52. Constant et al., <i>Some Properties of amorphous SiXC1-x (H) alloys prepared by CVD from various organosilicon compounds</i> , Solid State Chemistry, 1982, pp. 267-270
	53. Deville et al., <i>An AES study of the influence of carbon on the chemical structure of some oxide films deposited by PECVD of organosilicon precursors</i> , Applied Surface Science 137 (1999) 136-141
	54. Fonseca et al., <i>Plasma Polymerization of Tetramethylsilane</i> , Am. Chemical Society, 1993, 5, 1676-1682
	55. H. Beckers, et al., "Synthesis and Properties of (Trifluoromethyl) trichlorosilane, a Versatile Precursor for CF3Si Compounds," J. Organometal. Chem., Vol. 316, pp. 41-50, (1986).
	56. Indrajit Banerjee, et al., "Characterization of Chemical Vapor Deposited Amorphous Fluorocarbons for Low Dielectric Constant Interlayer Dielectrics," J. Electrochem. Soc., Vol. 146(6), p. 2219 (1999).
	57. Inoue et al., <i>Mass spectroscopy in plasma-enhanced chemical vapor deposition of silicon-oxide films using tetramethoxysilane</i> , Thin Solid Films 316 (1998) 79-84
	58. Inoue et al., <i>Spectroscopic studies on preparation of silicon oxide films by PECVD using organosilicon compounds</i> , Plasma Sources Sci. Technol. 5 (1996) 339-343
	59. K.G. Sharp and T.D. Coyle, "Synthesis and Some Properties of Trifluoro(trifluoromethyl) silane," J. Fluorine Chem., Vol. Q, pp. 249-251 (1971/72).
	60. Limb, Scott J., et al., "Growth of fluorocarbon polymer thin films with high CF2 fractions and low dangling bond concentrations by thermal chemical vapor deposition," App. Phys. Lett., Vol. 68(20), p. 2810 (1996).
	61. Loboda, M.J., <i>New solutions for intermetal dielectrics using trimethylsilane-based PECVD processes</i> , Microelectronic Engineering 50 (2000) 15-23
	62. Matsuki, N., U.S. Patent Application No. 09/243,156 <i>Silicone Polymer insulation film on semiconductor substrate and method for forming the film</i> , filed February 2, 1999.
	63. Nguyen et al., <i>Plasma organosilicon polymers</i> , J. Electrochem. Soc., August 1985, pp. 1925-1932
	64. Sang-Soo Han, et al., "Deposition of Fluorinated Amorphous Carbon Thin Films as a Low-Dielectric Constant Material," J. Electrochem. Soc., Vol. 146(9), p.3383 (1999).
	65. Savage, Charles R., et al., "Spectroscopic Characterization of Films Obtained in Pulsed Radio-Frequency Plasma Discharges of Fluorocarbon Monomers," Structure-Property Relations in Polymers, pp. 745-768, American Chemical Society, (1993).
	66. Sharp, K.G., et al., "Perfluoro(alkylsilanes). II: Trifluoro(trifluoromethyl) silane and Trifluoro(pentafluoroethyl) silane," Inorg. Chem., Vol. 11, No. 6, pp. 1259-1264, (1972).
	67. Shirafuji et al., <i>PE-CVD of fluorocarbon/silicon oxide composite thin films from TFE and HMDSO</i> , Mat. Res. Soc. Symp. Proc. Vol. 544, pp. 173-178
	68. Shirafuji et al., <i>PE-CVD of Fluorocarbon/SiO composite thin films using C4F8 and HMDSO1</i> , Plasmas and Polymers, Vo. 4, No. 1, 1999, pp. 57-75
<b>A</b>	69. Shirafuji et al., <i>Plasma copolymerization of tetrafluoroethylene/hexamethyldisiloxane and In Situ Fourier Transform infrared spectroscopy of its gas phase</i> , Jpn. J. Appl. Phys. Vol. 38 (1999) pp. 4520-4526

EXAMINER 	DATE CONSIDERED <b>11/05</b>
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	APPLICANT Michael A. Todd	
	FILING DATE Filed Herewith	GROUP Unknown

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
A	70. Sugahara et al., <i>Low Dielectric constant carbon containing SiO2 films deposited by PECVD technique using a novel CVD precursor</i> , DUMIC Conference, Feb. 10-11, 1997, pp. 19-25
	71. Thomas et al., <i>Plasma etching and surface analysis of a SiC:H films deposited by low temperature plasma enhanced chemical vapor deposition</i> , Mat. Res. Soc. Symp. Proc. Vol. 334, 1994, pp. 445-450
	72. Varma, Ravi, "Organosilylation: Synthesis and Characterization of Silylmethyl Methyl Ether," INORG. NUCL. CHEM. LETTERS, Vol. 6, pp. 9-14, 1970.
A	73. Washburne, Stephen S., et al. "Chloraminosilanes: I: The Preparation of Chloro(Dimethylamino) Hydrogen Silanes," Inorg. Nucl. Chem. Letters Vol. 5, pp. 17-19, Pergamon Press.

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